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AMENDMENTS TO THE CLAIMS

Please amend the current claims as follows:

Claims 1 – 10 (Cancelled)

11. (Currently Amended) A method for making a nitride light emitting structure comprising the operations of:

providing a ridge structure having an active region;

adding a burying layer including nitride, the material in the burying layer doped throughout in one of a group of n-doped, p-doped or undoped, the burying layer overlying said ridge structure, said ridge structure forming a guiding surface where the burying layer contacts the active region, the guiding surface providing index guiding in the ridge structure during operation of the light emitting structure.

12. (Previously Presented) The method of Claim 11 wherein the ridge structure includes a lower cladding layer below the active region, said lower cladding layer being a shortperiod superlattice.

13. (Original) The method of Claim 11 wherein said ridge structure is oriented along the <1100> crystallographic direction.

14. (Currently amended.) The method of claim 11 wherein said burying layer is p-doped throughout.

15. (Previously Presented) The method of Claim 11 wherein a tunnel barrier layer adjoins a multiple quantum well structure in the ridge structure.

16. (Currently Amended) A method for making a nitride light emitting structure comprising the operations of:

providing a ridge structure having a multiple quantum well structure;

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adding a first burying layer including nitride overlying said ridge structure, the first burying layer doped throughout with a single carrier type of one of a group of either n type, p type or intrinsic, said first burying layer having an opening to said third surface of said ridge structure for electrical contact, a guiding surface forming where the first burying layer contacts the multiple quantum well structure, the guiding surface providing index guiding in the ridge structure during operation of the light emitting structure; and

adding a second burying layer overlying said first burying layer, such that said second burying layer is in contact with said a top surface of said ridge structure.

17. (Original) The method of Claim 16 wherein said first burying layer is n-doped.

18. (Original) The method of Claim 16 wherein said second burying layer is comprised of magnesium doped GaN.

19. (Original) The method of Claim 16 wherein said ridge structure is oriented along the <1100> crystallographic direction.

20. (Original) The method of Claim 16 wherein said cladding structure is a shortperiod superlattice.

21. (Previously presented) The method of Claim 16 wherein the operation of providing a ridge structure is an etching process.

22. (Previously presented) The method of Claim 21 wherein the etching is a reactive ion etch.

23. (Previously presented) The method of Claim 21 wherein the etching is an ion beam etching.

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24. (Previously presented) The method of Claim 16 wherein the operation of adding a first burying layer is by growing the first burying layer.

25. (Previously presented) The method of Claim 22 wherein a metal organic chemical vapor deposition is used in the growing process.

26. (Previously presented) The method of Claim 23 wherein the opening in the burying layer is formed by etching the burying layer.

27. (Previously presented) The method of Claim 11 wherein the providing of the ridge structure uses an etching process.

28. (Previously presented) The method of Claim 27 wherein the etching process is a reactive ion etch.

29. (Previously presented) The method of Claim 27 wherein the etching process is an ion beam etch.

30. (Previously presented) The method of Claim 27 wherein the etching process is a chemical assisted ion beam etching process.

31. (Previously presented) The method of Claim 27 wherein the etching process is an inductively coupled plasma etch.

32. (Previously presented) The method of Claim 11 wherein the operation of adding a burying layer involves growing the burying layer.

33. (Previously presented) The method of Claim 11 wherein metal organic chemical vapor deposition is used to grow the burying layer.

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34. (Previously presented) The method of Claim 11 further comprising the operation of:

etching an opening into the burying layer, the opening to provide an electrical contact.

35. (New) The method of claims 16 wherein the first burying layer is p-doped.

36. (New) A method for making a nitride light emitting structure comprising the operations of:

providing a ridge structure having an active region;

adding a burying layer including nitride, the burying layer n-doped throughout, the burying layer overlying said ridge structure, said ridge structure forming a guiding surface where the burying layer contacts the active region, the guiding surface providing index guiding in the ridge structure during operation of the light emitting structure..

37. (New) A method for making a nitride light emitting structure comprising the operations of:

providing a ridge structure having an active region;

epitaxially depositing a burying layer including nitride, the burying layer undoped throughout, the burying layer overlying said ridge structure, said ridge structure forming a guiding surface where the burying layer contacts the active region, the guiding surface providing index guiding in the ridge structure during operation of the light emitting structure..